

as to ensure uniform irradiation of the whole volume of the crystal. The samples were irradiated at temperatures no higher than 100°K. The measurements were carried out in an URS-50IM diffractometer.

In Fig. 1a we illustrate the relative change in the intensities of certain diffraction lines of the test samples after subjection to electron irradiation.

It should be noted that after irradiation there is a certain fall in the line intensities of the polycrystalline aggregates; this may be associated with the formation of defect complexes and the pinning of these at grain boundaries [1]. The effect is stronger for proton irradiation owing to the greater defect density (Fig. 1b). The considerable increase in background furthermore supports this fact [2]. The unit in Fig. 1 is taken as the line intensity of the samples before irradiation I_0 . In the case of the single crystals the change in intensity diminishes as the impurity content increases. The principal change in the intensity occurs for the lines of the family of planes which have predominantly covalent bonds. Similar effects were observed when studying the effect of plastic deformation on the structure of bismuth alloys.

Further investigations are required in order to explain these phenomena.

LITERATURE CITED

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